

DFH10T

Diffused Junction Type Silicon Diode

1.0A Power Rectifier

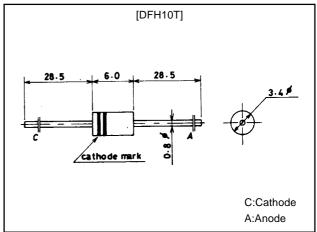
Features

- · High-speed switching use.
- · Plastic molded structure.
- \cdot Reverse recovery time trr=0.15 μ s max (B, C, E, G). trr=0.3 μ s max (J, L, N, R).
- \cdot Peak reverse voltage: V_{RM} =100 to 1500V
- · Average rectified current I_O=1.0A

Package Dimensions

unit:mm

1175



Specifications

Absolute Maximum Ratings at Ta = 25°C

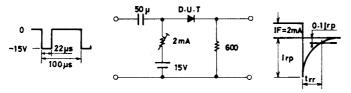
Parameter	Symbol	Conditions	DFH10TB	DFH10TC	DFH10TE	DFH10TG	Unit
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Peak Reverse Voltage	V _{RM}		100	200	400	600	V
Average Rectified Current	Io	Ta=25°C	\rightarrow	\rightarrow	\rightarrow	1.0	Α
Surge Forward Current	I _{FSM}	50Hz sine wave, 1 cycle	\rightarrow	\rightarrow	\rightarrow	60	Α
Junction Temperature	Tj		\rightarrow	\rightarrow	\rightarrow	150	°C
Storage Temperature	Tstg		\rightarrow	\rightarrow	\rightarrow	-40 to +150	°C

Parameter	Symbol	Conditions	DFH10TJ	DFH10TL	DFH10TN	DFH10TR	Unit
Peak Reverse Voltage	V _{RM}		800	1000	1200	1500	V
Average Rectified Current	lo	Ta=25°C	\rightarrow	\rightarrow	\rightarrow	1.0	Α
Surge Forward Current	I _{FSM}	50Hz sine wave, 1 cycle	\rightarrow	\rightarrow	\rightarrow	40	Α
Junction Temperature	Tj		\rightarrow	\rightarrow	\rightarrow	125	°C
Storage Temperature	Tstg		\rightarrow	\rightarrow	\rightarrow	-40 to +150	°C

Electrical Characteristics at Ta = 25°C

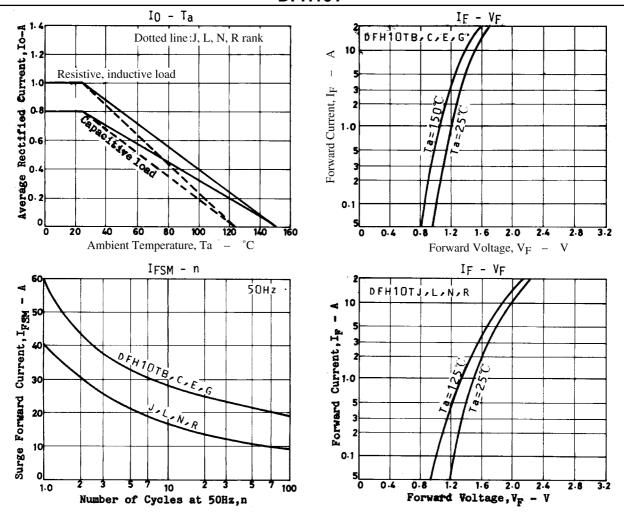
Parameter	Symbol	Conditions	Ratings			Unit
Falametei	Syllibol	Conditions		typ	max	
Forward Voltage	٧ _F	I _F =1.0A (B, C, E, G)			1.2	V
		I _F =1.0A (J, L, N, R)			1.5	V
Reverse Current	I _R	V _R :At each V _{RM}			10	μA
Reverse Recovery Time	t _{rr}	I _F =2mA, V _R =15V (B,C, E, G)			0.15	μs
		I _F =2mA, V _R =15V (J, L, N, R)			0.3	μs

Reverse Recovery Time Test Circuit



Unit (resistance: Ω , capacitance:F)

DFH10T



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